

## SANYO Semiconductors

DATA SHEET



# N-Channel Silicon MOSFET 2SK4063LS — General-Purpose Switching Device **Applications**

#### **Features**

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- High reliability (Adoption of HVP process).
- Attachment workability is good by Mica-less package.
- · Avalanche resistance guarantee.

## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		500	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	IDc*1	Limited only by maximum temperature	16	Α
	I <sub>Dpack</sub> *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	11.5	Α
Drain Current (Pulse)	IDP		64	Α
Allowable Power Dissipation	PD		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		798	mJ
Avalanche Current *5	IAV		16	Α

\*1 Shows chip capability

\*2 Package limited

\*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

\*4 VDD=99V, L=5mH, IAV=16A

\*5 L≤5mH, single pulse

Marking: K4063

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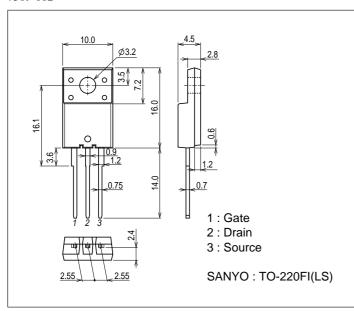
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### Electrical Characteristics at Ta=25°C

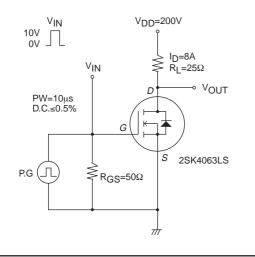
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	500			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V			±100	nA
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	3		5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =8A	6	12		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)	ID=8A, VGS=15V		0.3	0.39	Ω
Input Capacitance	Ciss	V <sub>DS</sub> =30V, f=1MHz		2150		pF
Output Capacitance	Coss	V <sub>DS</sub> =30V, f=1MHz		230		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =30V, f=1MHz		15		pF
		V <sub>DS</sub> =5V, f=1MHz		31		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		55		ns
Rise Time	tr	See specified Test Circuit.		170		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		63		ns
Fall Time	tf	See specified Test Circuit.		83		ns
Total Gate Charge	Qg	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =16A		40		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =16A		15.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =16A		15.2		nC
Diode Forward Voltage	VSD	IS=16A, VGS=0V		0.95	1.2	V

#### **Package Dimensions**

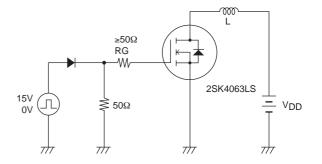
unit : mm (typ) 7509-002



#### Switching Time Test Circuit



#### Avalanche Resistance Test Circuit



IT10982

125

150

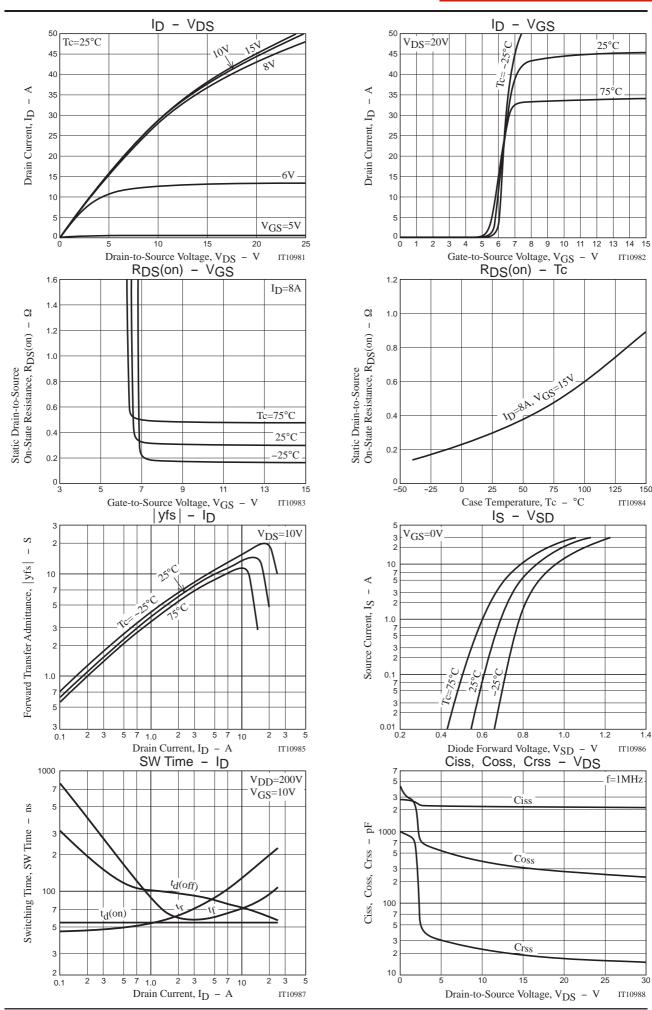
1.4

IT10986

f=1MHz

IT10984

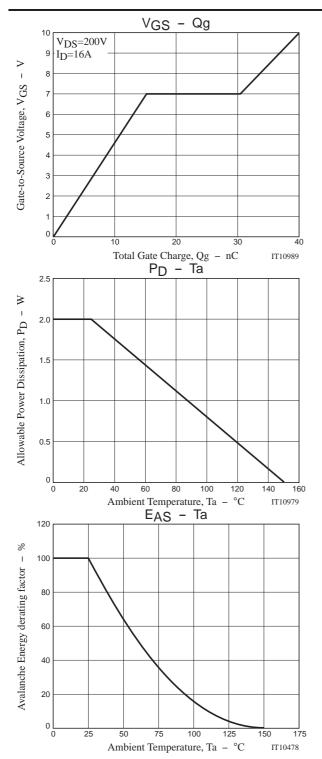
2SK4063LS

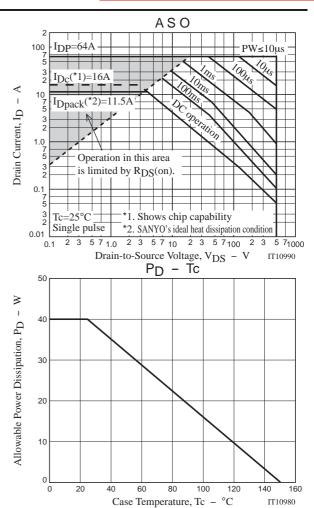


IT10988

30

2SK4063LS





Note on usage : Since the 2SK4063LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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